

## Features

- Optimized for Broadband Operation (DC - 4 GHz)
- 25 W P3dB CW Power @ 3000 MHz
- 16 - 20 W P3dB CW Power from 1.0 - 2.5 GHz in application board with >45% Drain Efficiency
- 10 - 20 W P3dB CW Power from 0.03 - 1.0 GHz in application board with >50% Drain Efficiency
- High Efficiency from 14 to 28 V
- 4°C/W  $R_{TH}$  with  $T_J < 200^\circ\text{C}$
- Robust up to 10:1 VSWR Mismatch at All Angles with No Device Damage at 90°C Flange
- Subject to EAR99 Export Control
- RoHS\* Compliant

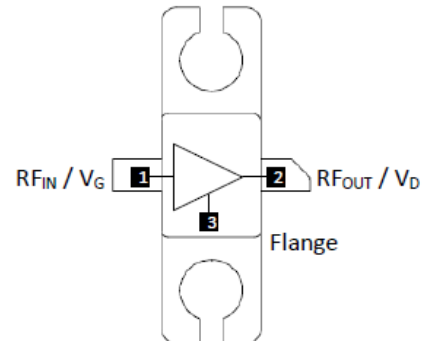
## Applications

- Defense Communications
- Land Mobile Radio
- Avionics
- Wireless Infrastructure
- ISM
- VHF/UHF/L/S-Band Radar

## Description

The NPT1012B GaN HEMT is a power transistor optimized for DC - 4 GHz operation. This device supports CW, pulsed, and linear operation with output power levels to 25 W. This transistor is assembled in an industry standard surface mount plastic package.

## Functional Schematic



## Pin Configuration

Pin #	Pin Name	Function
1	RF <sub>IN</sub> / V <sub>G</sub>	RF Input / Gate
2	RF <sub>OUT</sub> / V <sub>D</sub>	RF Output / Drain
3	Flange <sup>1</sup>	Ground / Source

1. The flange must be connected to RF and DC ground. This path must also provide a low thermal resistance heat path.

## Ordering Information

Part Number	Package
NPT1012B	30 slot tray

\* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

# GaN Power Transistor, 28 V, 25 W DC - 4 GHz



NPT1012B

Rev. V1

**Typical CW RF Specifications: (measured in a test fixture)**  
**Freq. = 3 GHz,  $V_{DS} = 28$  V,  $I_{DQ} = 225$  mA,  $T_C = 25^\circ\text{C}$**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Average Output Power	3 dB Compression 1 dB Compression	$P_{3dB}$ $P_{1dB}$	43 —	44 43	—	W
Small Signal Gain	—	$G_{SS}$	12	13	—	dB
Drain Efficiency	3 dB Compression	$\eta$	57	65	—	%
Output Mismatch Stress	VSWR = 10:1. all phase angles, $P_{OUT} = P_{SAT}$	$\psi$	No performance degradation after test			

## DC Electrical Characteristics: $T_C = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{GS} = -8$ V, $I_D = 8$ mA	$V_{BDS}$	100	—	—	V
Drain-Source Leakage Current	$V_{GS} = -8$ V, $V_{DS} = 60$ V	$I_{DLK}$	—	—	4	mA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{DS} = 28$ V, $I_D = 8$ mA	$V_T$	-2.3	-1.8	-1.3	V
Gate Quiescent Voltage	$V_{DS} = 28$ V, $I_D = 225$ mA	$V_{GSQ}$	-2.0	-1.5	-1.0	V
On Resistance	$V_{GS} = 2$ V, $I_D = 60$ mA	$R_{ON}$	—	0.44	0.55	$\Omega$
Drain Current	$V_{DS} = 7$ V pulsed, pulse width 300 $\mu\text{s}$ 0.2% Duty Cycle, $V_{GS} = 2$ V	$I_D$	—	5.4	—	A

**Absolute Maximum Ratings<sup>2,3,4</sup>**

Parameter	Absolute Maximum
Drain Source Voltage, $V_{DS}$	100 V
Gate Source Voltage, $V_{GS}$	-10 to 3 V
Gate Current, $I_G$	40 mA
Total Device Power Dissipation (derated above +25°C)	44 W
Junction Temperature, $T_J$	+200°C
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

- 2. Exceeding any one or combination of these limits may cause permanent damage to this device.
- 3. MACOM does not recommend sustained operation near these survivability limits.
- 4. Operating at nominal conditions with  $T_J \leq 200^\circ\text{C}$  will ensure  $\text{MTTF} > 1 \times 10^6$  hours.

**Thermal Characteristics<sup>5</sup>**

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance	$V_{DS} = 28 \text{ V}, T_J = 180^\circ\text{C}$	$R_{\theta JC}$	4.0	°C/W

- 5. Junction temperature ( $T_J$ ) measured using IR Microscopy. Case temperature measured using thermocouple embedded in heat-sink.

**Handling Procedures**

Please observe the following precautions to avoid damage:

**Static Sensitivity**

Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these MM Class A, CDM Class IV, HBM Class 1B devices.

Load-Pull Data, Reference Plane at Device Leads:  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 225\text{ mA}$ ,  $T_A = 25^\circ\text{C}$

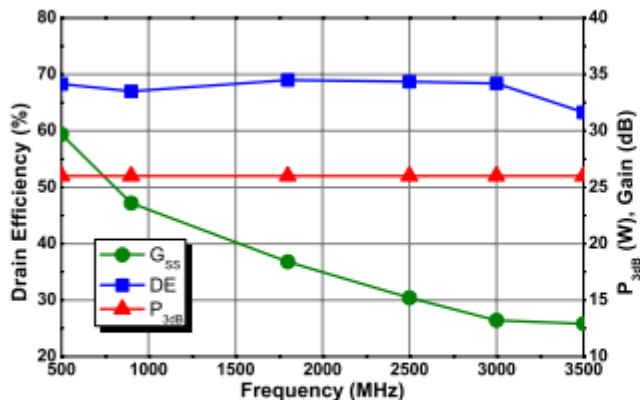


Figure 1 - Typical CW Performance in Load-Pull,  $V_{DS} = 28\text{V}$ ,  $I_{DQ} = 225\text{mA}$

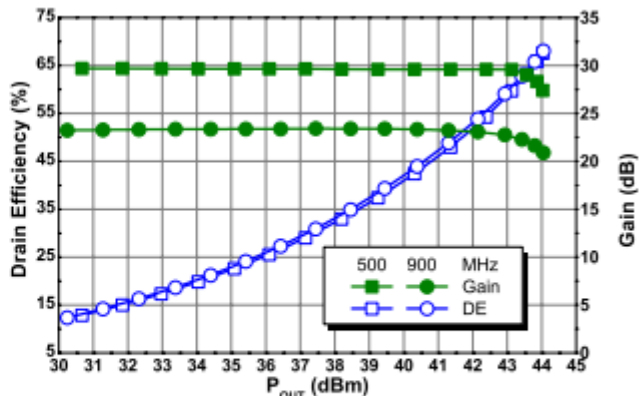


Figure 2 - Typical CW Performance<sup>1</sup> in Load-Pull,  $V_{DS} = 28\text{V}$ ,  $I_{DQ} = 225\text{mA}$

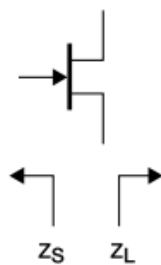
Load-Pull Data, Reference Plane at Device Leads:  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 225\text{ mA}$ ,  $T_C = 25^\circ\text{C}$

**Table 1: Optimum Impedance Characteristics for CW Gain, Drain Efficiency, and Output Power Performance**

Frequency (MHz)	$V_{DS}$ (V)	$Z_S$ ( $\Omega$ )	$Z_L$ ( $\Omega$ )	$P_{SAT}$ (W)	GSS (dB)	Drain Efficiency @ $P_{SAT}$ (%)
500 <sup>6</sup>	14	7.0 + j8.2	8.6 + j7.4	12	27.8	76
500 <sup>6</sup>	22	7.0 + j8.2	9.7 + j11.3	21	29.2	74
500 <sup>6</sup>	28	7.0 + j8.2	9.7 + j14.1	26	29.7	68
900 <sup>6</sup>	14	5.8 + j3.1	6.8 + j4.7	12	22.4	74
900 <sup>6</sup>	22	5.8 + j3.1	9.6 + j5.3	24	23.3	74
900 <sup>6</sup>	28	5.8 + j3.1	9.8 + j7.8	26	23.6	67
1800	28	3.5 - j3.6	6.9 + j2.0	26	18.4	69
2500	14	3.9 - j7.5	6.2 - j8.0	13	13.7	70
2500	22	4.8 - j7.0	5.5 - j4.1	19	14.9	69
2500	28	4.8 - j7.0	5.5 - j4.1	26	15.2	69
3000	28	5.3 - j8.8	5.3 - j6.4	26	13.2	66
3500	28	5.0 - j14.5	7.0 - j9.5	26	12.9	63

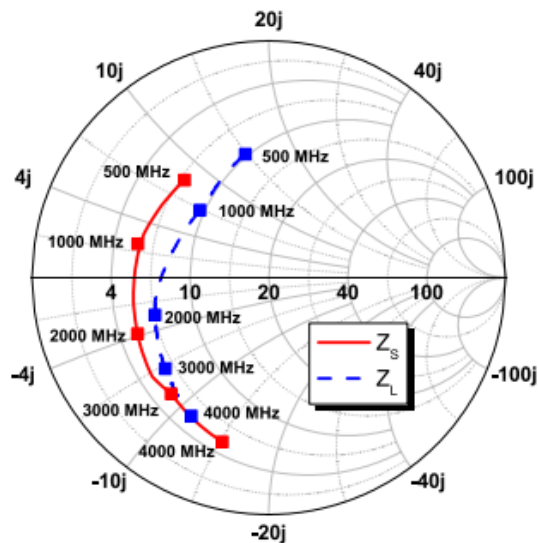
6. 500 MHz and 900 MHz Load-Pull data collected using a 4.7  $\Omega$  resistor in the RF path added for stability.

**Impedance Reference**



$Z_S$  is the source impedance presented to the device.  
 $Z_L$  is the load impedance presented to the device.

**$Z_S$  and  $Z_L$  vs. Frequency**



**Figure 3 - Optimum Impedances for CW Performance,  $V_{DS} = 28\text{V}$**

Load-Pull Data, Reference Plane at Device Leads:  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 225\text{ mA}$ ,  $T_A = 25^\circ\text{C}$

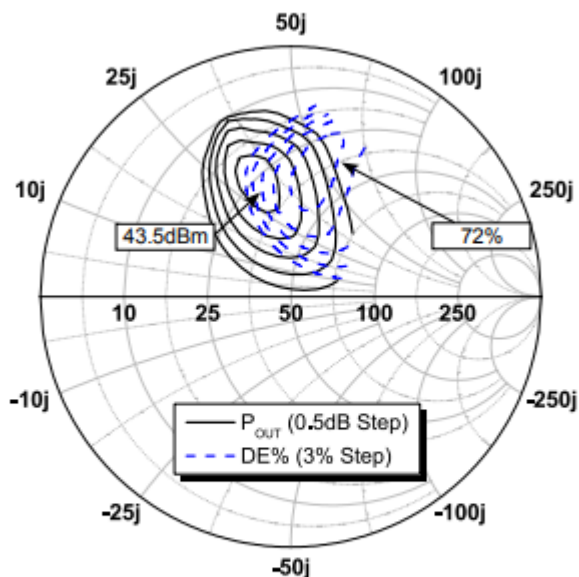


Figure 4 - Load-Pull Contours<sup>1</sup>, 500MHz,  
 $P_{IN} = 14.5\text{dBm}$ ,  $Z_S = 7.0 + j8.2\ \Omega$

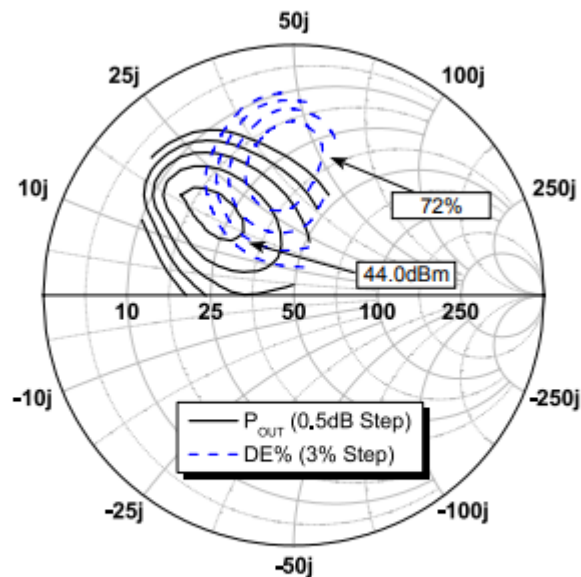


Figure 5 - Load-Pull Contours<sup>1</sup>, 900MHz,  
 $P_{IN} = 21.0\text{dBm}$ ,  $Z_S = 5.8 + j3.1\ \Omega$

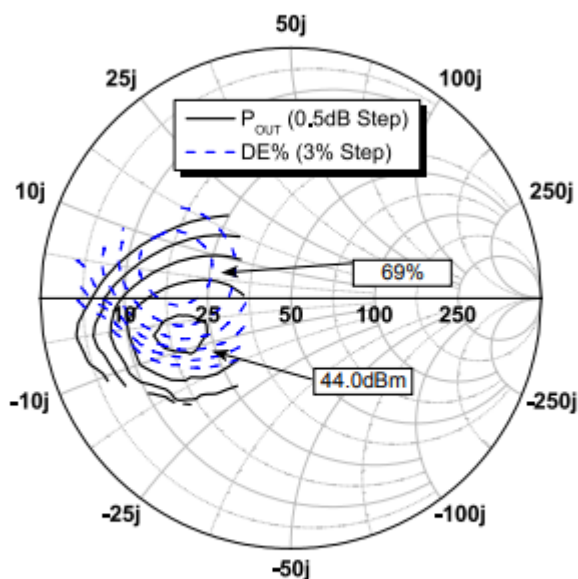


Figure 6 - Load-Pull Contours, 1800MHz,  
 $P_{IN} = 26.5\text{dBm}$ ,  $Z_S = 3.5 - j3.6\ \Omega$

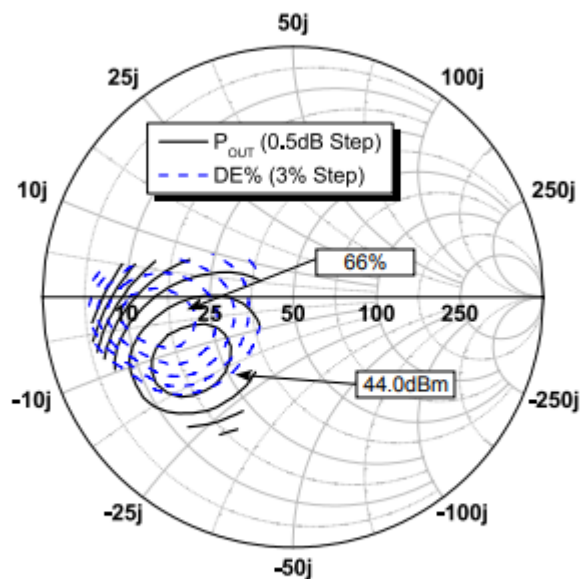


Figure 7 - Load-Pull Contours, 2500MHz,  
 $P_{IN} = 29.4\text{dBm}$ ,  $Z_S = 4.8 - j7.0\ \Omega$

Load-Pull Data, Reference Plane at Device Leads:  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 225\text{ mA}$ ,  $T_A = 25^\circ\text{C}$

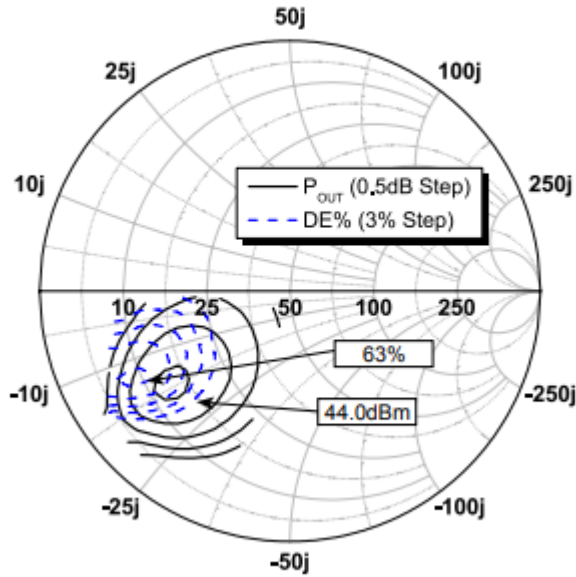


Figure 8 - Load-Pull Contours, 3000MHz,  
 $P_{IN} = 31.7\text{dBm}$ ,  $Z_S = 5.3 - j8.8\ \Omega$

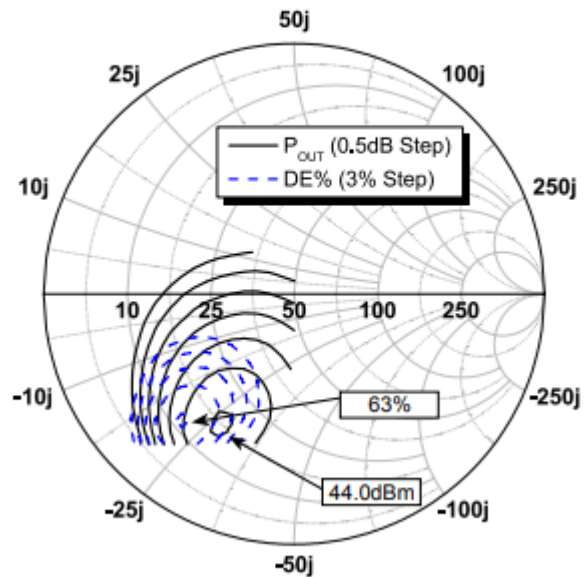


Figure 9 - Load-Pull Contours, 3500MHz,  
 $P_{IN} = 33.5\text{dBm}$ ,  $Z_S = 5.0 - j14.5\ \Omega$

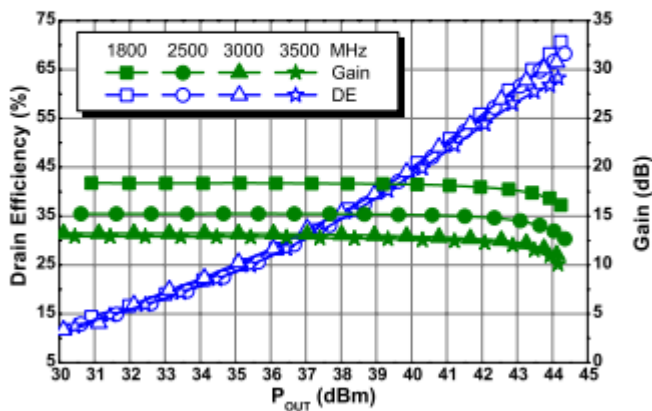


Figure 10 - Typical CW Performance in Load-Pull

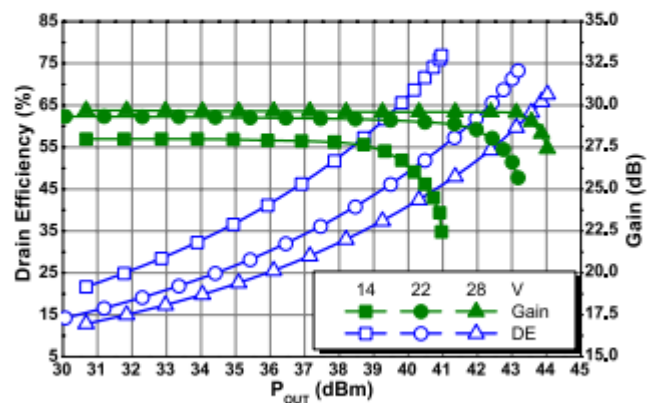


Figure 11 - Typical CW Performance<sup>1</sup> Over Voltage in Load-Pull, 500MHz



Load-Pull Data, Reference Plane at Device Leads:  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 225\text{ mA}$ ,  $T_A = 25^\circ\text{C}$

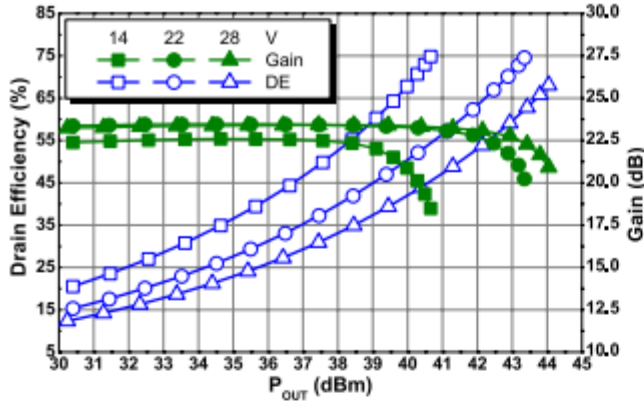


Figure 12 - Typical CW Performance<sup>1</sup> Over Voltage in Load-Pull, 900MHz

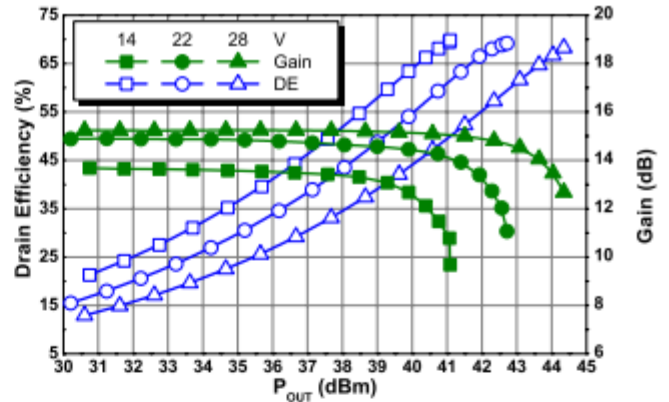


Figure 13 - Typical CW Performance Over Voltage in Load-Pull, 2500MHz

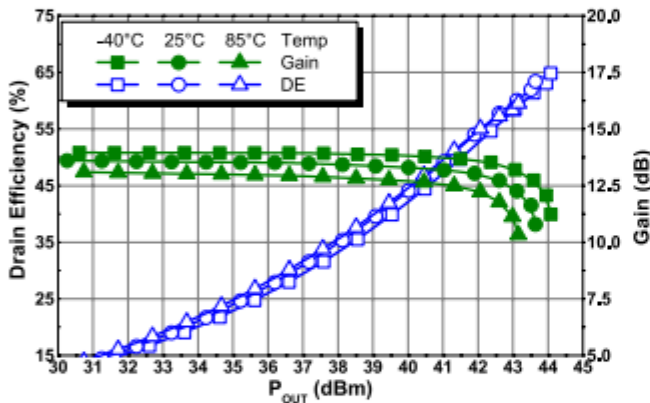


Figure 14 - Typical CW Performance Over Temperature in Nitronex Test Fixture, 3000MHz

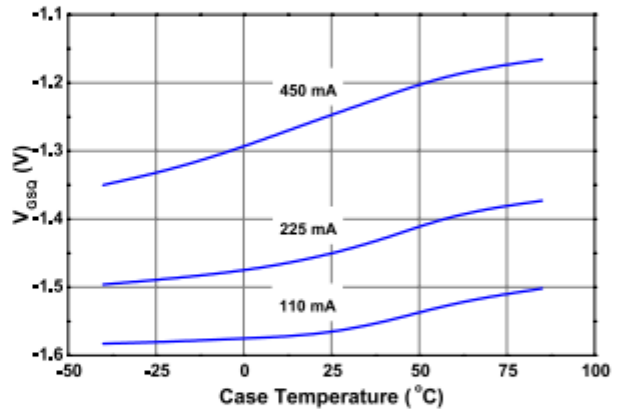


Figure 15 - Quiescent Gate Voltage ( $V_{GSQ}$ ) Required to Reach  $I_{DQ}$  as a Function of Case Temperature,  $V_{DS} = 28\text{ V}$

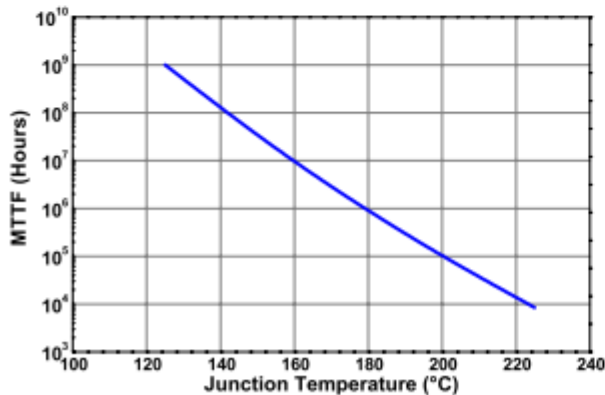


Figure 16 - MTTF of NRF1 Devices as a Function of Junction Temperature

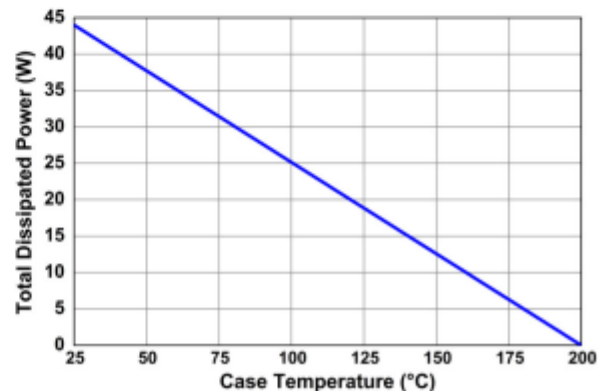
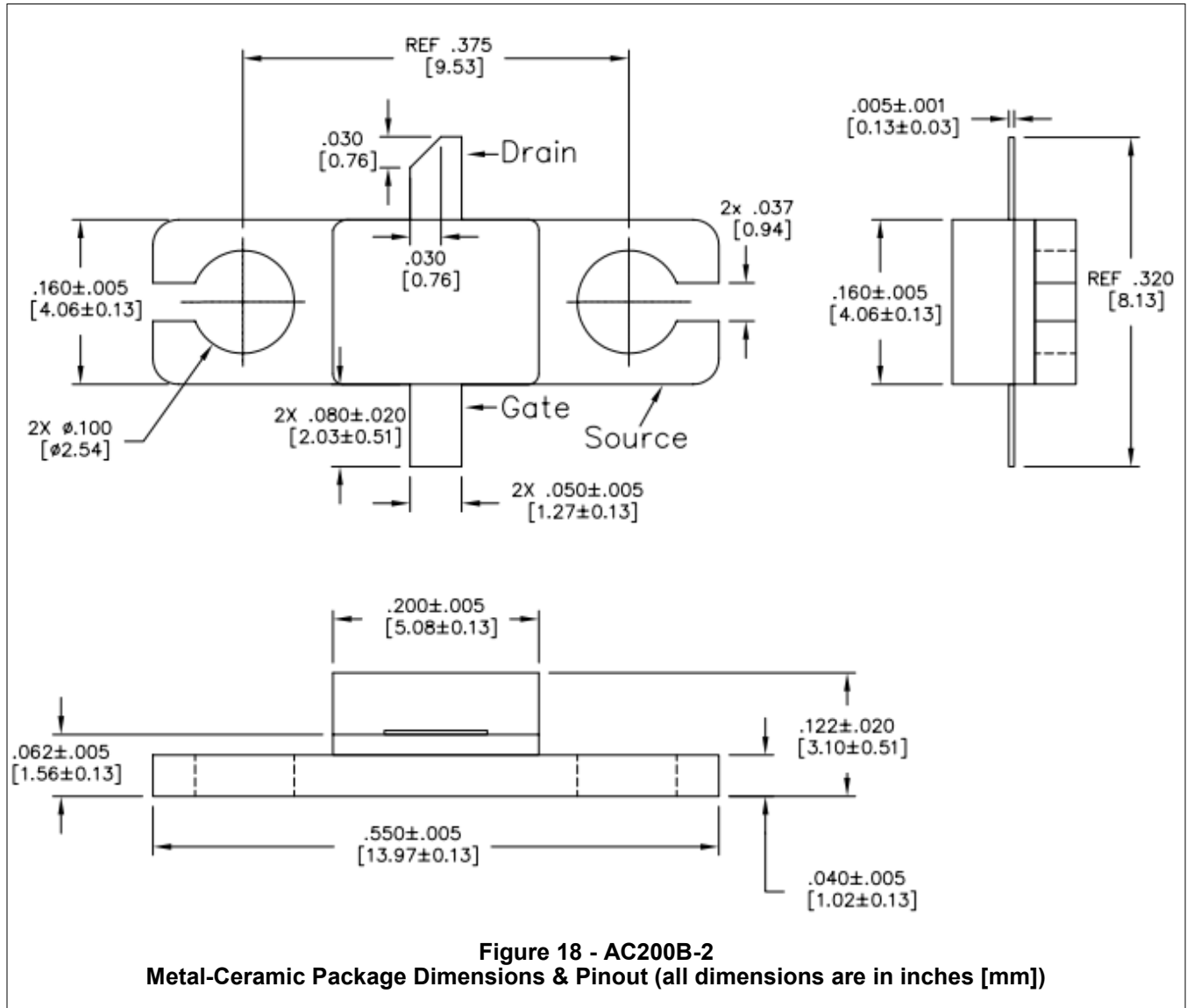


Figure 17 - Power Derating Curve



Outline Drawing



MACOM Technology Solutions Inc. ("MACOM"). All rights reserved.

These materials are provided in connection with MACOM's products as a service to its customers and may be used for informational purposes only. Except as provided in its Terms and Conditions of Sale or any separate agreement, MACOM assumes no liability or responsibility whatsoever, including for (i) errors or omissions in these materials; (ii) failure to update these materials; or (iii) conflicts or incompatibilities arising from future changes to specifications and product descriptions, which MACOM may make at any time, without notice. These materials grant no license, express or implied, to any intellectual property rights.

THESE MATERIALS ARE PROVIDED "AS IS" WITH NO WARRANTY OR LIABILITY, EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF MACOM PRODUCTS INCLUDING FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHT, ACCURACY OR COMPLETENESS, OR SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES WHICH MAY RESULT FROM USE OF THESE MATERIALS.

MACOM products are not intended for use in medical, lifesaving or life sustaining applications. MACOM customers using or selling MACOM products for use in such applications do so at their own risk and agree to fully indemnify MACOM for any damages resulting from such improper use or sale.

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [RF JFET Transistors](#) category:*

*Click to view products by [MACOM](#) manufacturer:*

Other Similar products are found below :

[CE3514M4](#) [CE3514M4-C2](#) [CE3520K3-C1](#) [CE3521M4](#) [CE3521M4-C2](#) [CE3512K2-C1](#) [CE3520K3](#) [CG2H80030D-GP4](#) [TGF2023-2-02](#)  
[NPT1004D](#) [MAGX-011086](#) [NPT25015D](#) [JANTXV2N4858](#) [CGHV27015S](#) [NPT2021](#) [NPTB00025B](#) [TGF2965-SM](#) [QPD1009](#) [QPD1010](#)  
[2SK3557-6-TB-E](#) [J211\\_D74Z](#) [NPTB00004A](#) [MMBFJ211](#) [QPD0005TR13](#) [QPD0020](#) [QPD1006](#) [QPD1016](#) [QPD1025L](#) [QPD1029L](#)  
[QPD1881L](#) [T2G6001528-Q3](#) [SKY65050-372LF](#) [J304](#) [CGH27015F](#) [CGH27060F](#) [CGH55015F1](#) [CMPA801B030F](#) [GTVA262711FA-V2-R0](#)  
[GTVA262701FA-V2-R0](#) [CGH40006S](#) [CGH40010F](#) [CGH40025F](#) [CGH40045F](#) [CGH40120F](#) [CGH40180PP](#) [CGH55015F2](#) [CGH60008D](#)  
[CGH60030D](#) [CGHV14500F](#) [CGHV1F006S](#)